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| SANYO | No.930C | 2SB892/2SD1207 |
| | | PNP/NPN Epitaxial Planar Silicon Transistors |

Large-Current Switching Applications

APPLICATIONS

- Power supplies, relay drivers, lamp drivers, and automotive wiring

FEATURES

- FBET and MBIT processed (Original process of SANYO)
- Low saturation voltage
- Large current capacity and wide ASO

Values for 2SB892 shown in ()

ABSOLUTE MAXIMUM RATINGS/T_a=25°C

| | | | unit |
|---------------------------------|------------------|----------|------|
| Collector to base voltage | V _{CB0} | (-)60 | V |
| Collector to emitter voltage | V _{CE0} | (-)50 | V |
| Emitter to base voltage | V _{EBO} | (-)6 | V |
| Collector current | I _C | (-)2 | A |
| Collector Current(Pulse) | I _{CP} | (-)4 | A |
| Allowable collector dissipation | P _C | 1 | W |
| Junction temperature | T _j | 150 | °C |
| Storage ambient temperature | T _{stg} | -55~+150 | °C |

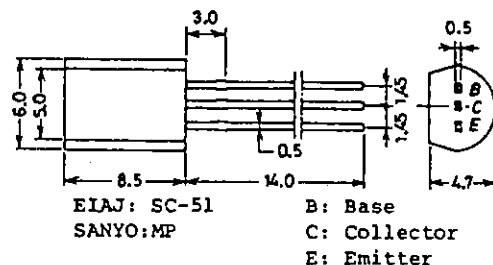
ELECTRICAL CHARACTERISTICS/T_a=25°C

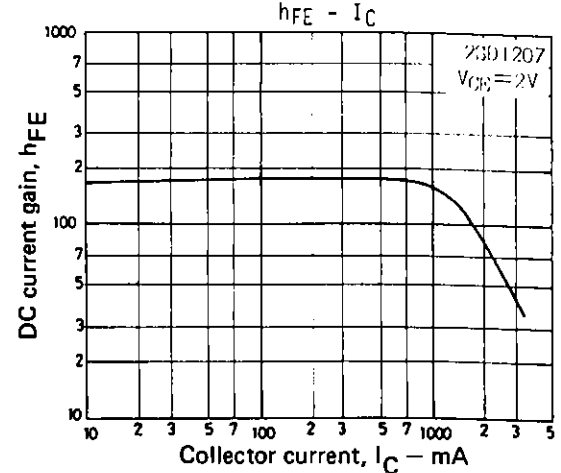
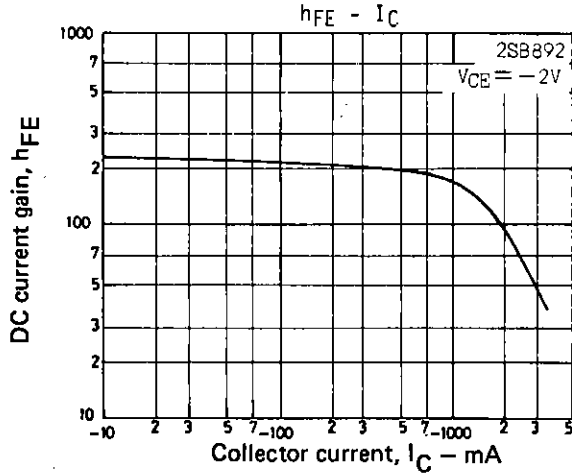
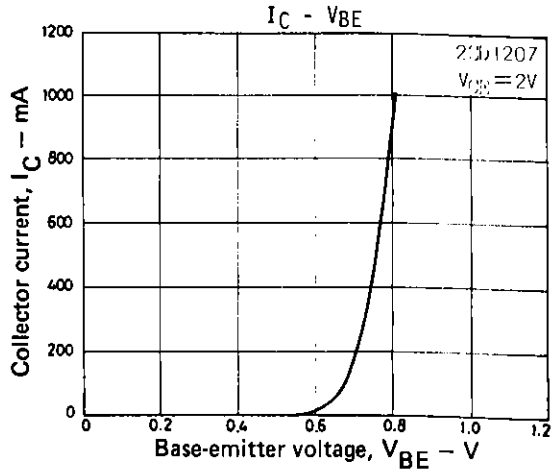
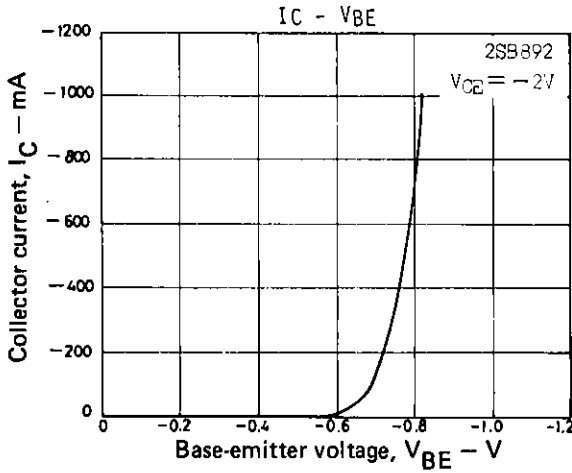
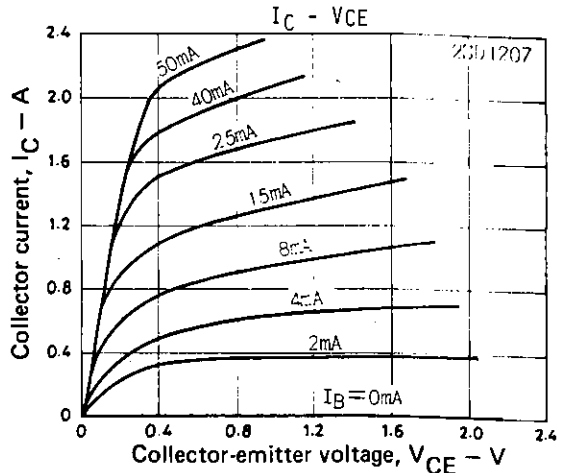
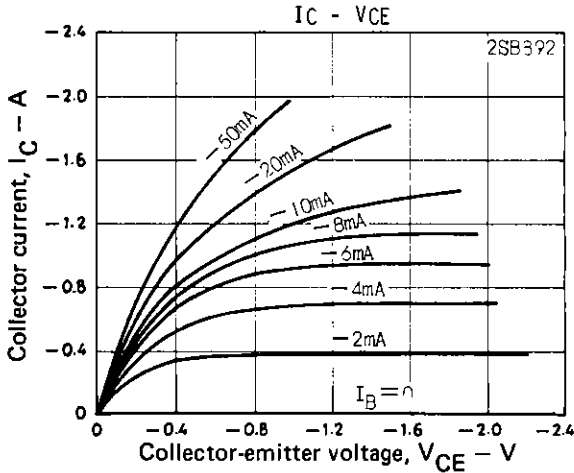
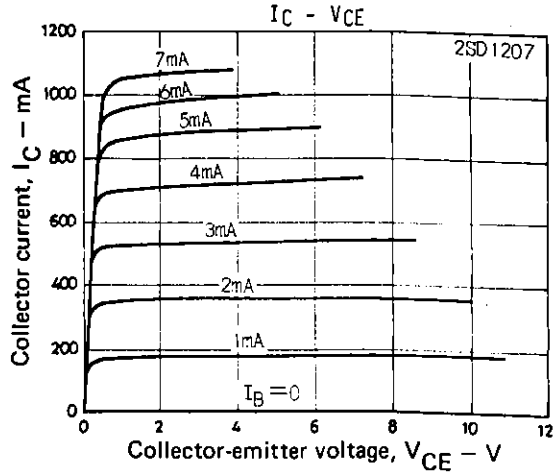
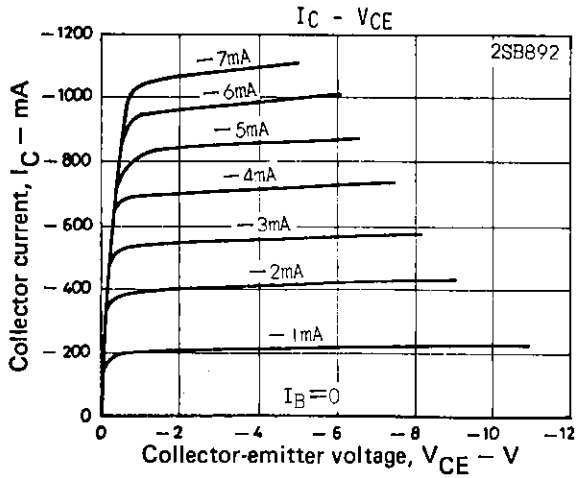
| | | | min | typ | max | unit |
|--------------------------------------|----------------------|--|--------|--------|--------|------|
| Collector cut-off current | I _{CBO} | V _{CB} =(-)50V, I _E =0 | | | (-)0.1 | μA |
| Emitter cut-off current | I _{EBO} | V _{EB} =(-)4V, I _C =0 | | | (-)0.1 | μA |
| DC current gain | h _{FE} (1)* | V _{CE} =(-)2V, I _C =(-)100mA | 100 | | 560 | |
| | | | 40 | | | |
| Gain-bandwidth product | f _T | V _{CE} =(-)10V, I _C =(-)50mA | | 150 | | MHz |
| | | | | | | |
| Output capacitance | c _{ob} | V _{CB} =(-)10V, f=1MHz | | 12 | | pF |
| | | | | (22) | | pF |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _C =(-)1A, I _B =(-)50mA | 0.15 | | 0.4 | V |
| | | | (-0.3) | | (-0.7) | V |
| Base-emitter saturation voltage | V _{BE(sat)} | I _C =(-)1A, I _B =(-)50mA | | (-)0.9 | (-)1.2 | V |
| Collector-base breakdown voltage | V _{(BR)CBO} | I _C =(-)10μA, I _E =0 | (-)60 | | | V |
| Collector-emitter breakdown voltage | V _{(BR)CEO} | I _C =(-)1mA, R _{BE} =∞ | (-)50 | | | V |
| Emitter-base breakdown voltage | V _{(BR)EBO} | I _E =(-)10μA, I _C =0 | (-)6 | | | V |

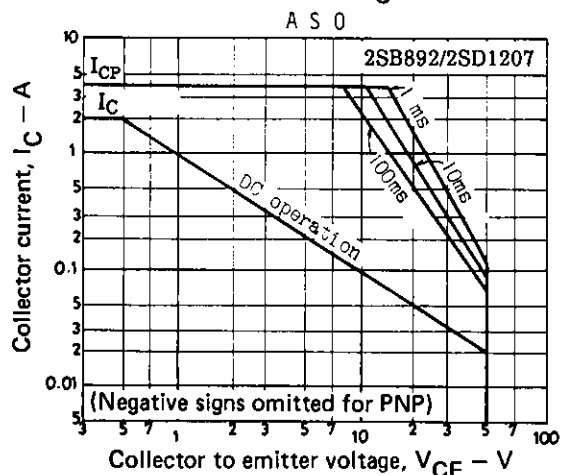
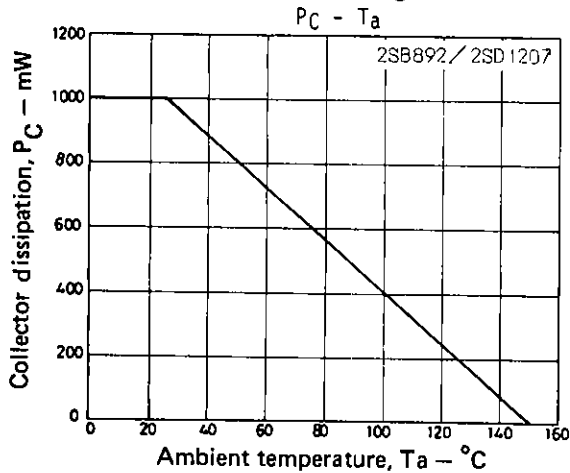
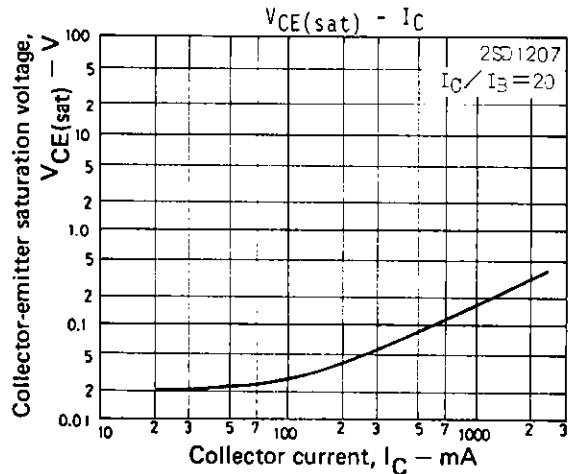
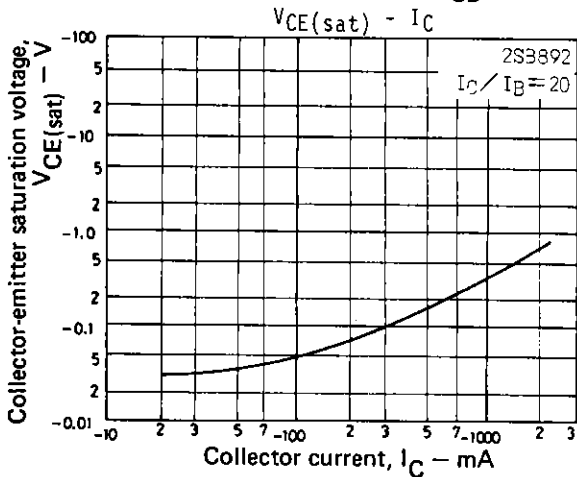
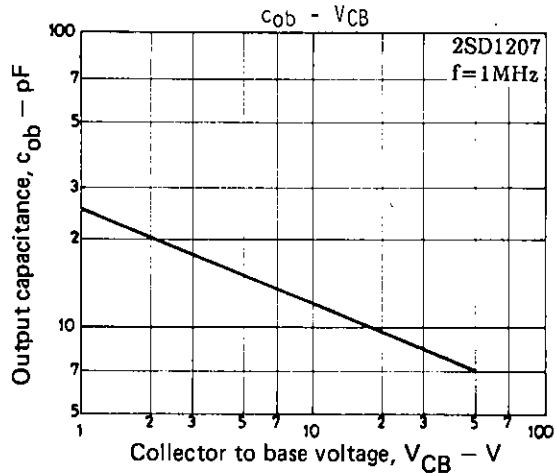
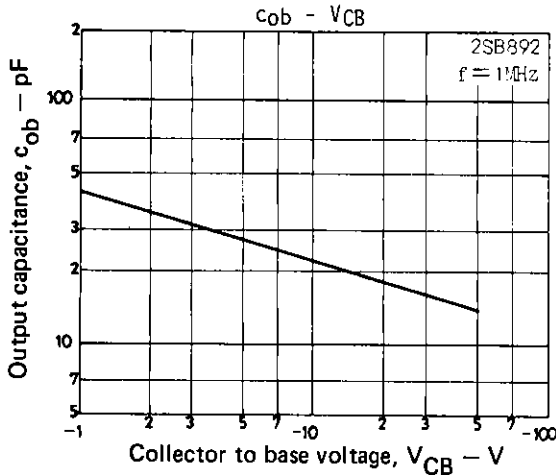
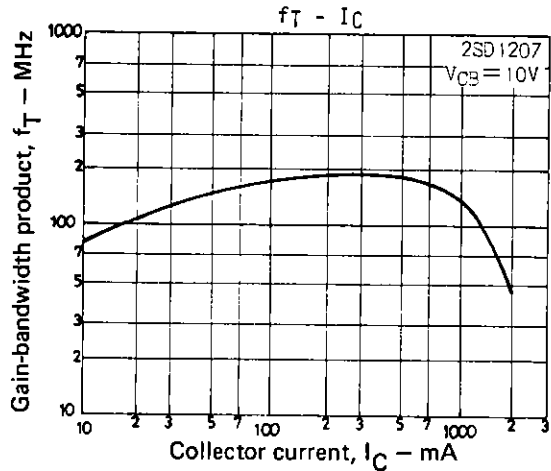
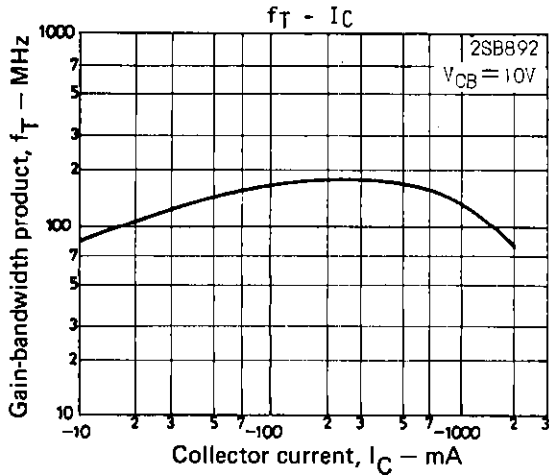
* 2SB892 and 2SD1207 are graded as follows by h_{FE} at 100mA:

| | | | | | | | | | | | |
|-----|---|-----|-----|---|-----|-----|---|-----|-----|---|-----|
| 100 | R | 200 | 140 | S | 280 | 200 | T | 400 | 280 | U | 560 |
|-----|---|-----|-----|---|-----|-----|---|-----|-----|---|-----|

Package Dimensions 2006A
(unit: mm)







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